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ABSTRACT OF THE DISCLOSURE

In a semiconductor device using a crystalline semiconductor film on a substrate 106 having an insulating surface, impurities are locally implanted into an active region 102 to form a pinning region 104. The pinning region 104 suppresses the spread of a depletion layer from the drain side to effectively prevent the short-channel effect. Also, since a channel forming region 105 is intrinsic or substantially intrinsic, a high mobility is realized.

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